

# Rong Zhang

## List of Publications by Citations

**Source:** <https://exaly.com/author-pdf/9625412/rong-zhang-publications-by-citations.pdf>

**Version:** 2024-04-23

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

264  
papers

3,650  
citations

31  
h-index

48  
g-index

290  
ext. papers

4,641  
ext. citations

4.6  
avg, IF

5.24  
L-index

#	Paper	IF	Citations
264	Planar carbon nanotube-graphene hybrid films for high-performance broadband photodetectors. <i>Nature Communications</i> , <b>2015</b> , 6, 8589	17.4	197
263	A robust and tuneable mid-infrared optical switch enabled by bulk Dirac fermions. <i>Nature Communications</i> , <b>2017</b> , 8, 14111	17.4	126
262	Extended vapor-liquid-solid growth and field emission properties of aluminium nitride nanowires. <i>Journal of Materials Chemistry</i> , <b>2003</b> , 13, 2024-2027		111
261	Solar-Blind Photodetector with High Avalanche Gains and Bias-Tunable Detecting Functionality Based on Metastable Phase HgO/ZnO Isotype Heterostructures. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2017</b> , 9, 36997-37005	9.5	106
260	Evidence of Both Surface and Bulk Dirac Bands and Anisotropic Nonsaturating Magnetoresistance in ZrSiS. <i>Advanced Electronic Materials</i> , <b>2016</b> , 2, 1600228	6.4	98
259	On the reverse gate leakage current of AlGaIn/GaN high electron mobility transistors. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 153503	3.4	92
258	High-Gain AlGaIn Solar-Blind Avalanche Photodiodes. <i>IEEE Electron Device Letters</i> , <b>2014</b> , 35, 372-374	4.4	76
257	Enhancing magnetic ordering in Cr-doped Bi <sub>2</sub> Se <sub>3</sub> using high-TC ferrimagnetic insulator. <i>Nano Letters</i> , <b>2015</b> , 15, 764-9	11.5	69
256	Forward tunneling current in GaN-based blue light-emitting diodes. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 083504	3.4	68
255	Carbonized Bamboos as Excellent 3D Solar Vapor-Generation Devices. <i>Advanced Materials Technologies</i> , <b>2019</b> , 4, 1800593	6.8	68
254	Electrical instability of amorphous indium-gallium-zinc oxide thin film transistors under monochromatic light illumination. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 243505	3.4	66
253	Ultra-Low Dark Current AlGaIn-Based Solar-Blind Metal-Semiconductor-Metal Photodetectors for High-Temperature Applications. <i>IEEE Sensors Journal</i> , <b>2012</b> , 12, 2086-2090	4	57
252	Evidence of weak localization in quantum interference effects observed in epitaxial La <sub>0.7</sub> Sr <sub>0.3</sub> MnO <sub>3</sub> ultrathin films. <i>Scientific Reports</i> , <b>2016</b> , 6, 26081	4.9	53
251	Sensitive and Ultrabroadband Phototransistor Based on Two-Dimensional Bi <sub>2</sub> O <sub>2</sub> Se Nanosheets. <i>Advanced Functional Materials</i> , <b>2019</b> , 29, 1905806	15.6	53
250	Progress on AlGaIn-based solar-blind ultraviolet photodetectors and focal plane arrays. <i>Light: Science and Applications</i> , <b>2021</b> , 10, 94	16.7	51
249	Enhanced bias stress stability of a-InGaZnO thin film transistors by inserting an ultra-thin interfacial InGaZnO:N layer. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 193505	3.4	50
248	Stable response to visible light of InGaIn photoelectrodes. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 262110	3.4	50

247	Atomic-Scale Magnetism of Cr-Doped Bi <sub>2</sub> Se <sub>3</sub> Thin Film Topological Insulators. <i>ACS Nano</i> , <b>2015</b> , 9, 10237-10247	4.7	46
246	Graphene-carbon nanotube hybrid films for high-performance flexible photodetectors. <i>Nano Research</i> , <b>2017</b> , 10, 1880-1887	10	44
245	High-Temperature Single Photon Detection Performance of 4H-SiC Avalanche Photodiodes. <i>IEEE Photonics Technology Letters</i> , <b>2014</b> , 26, 1136-1138	2.2	44
244	Room-temperature intrinsic ferromagnetism in epitaxial CrTe ultrathin films. <i>Nature Communications</i> , <b>2021</b> , 12, 2492	17.4	42
243	Raman and photoluminescence of ZnO films deposited on Si (111) using low-pressure metalorganic chemical vapor deposition. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2003</b> , 21, 979-982	2.9	41
242	High Color Rendering Index Hybrid III-Nitride/Nanocrystals White Light-Emitting Diodes. <i>Advanced Functional Materials</i> , <b>2016</b> , 26, 36-43	15.6	41
241	Highly Narrow-Band Polarization-Sensitive Solar-Blind Photodetectors Based on E <sub>GaO</sub> Single Crystals. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2019</b> , 11, 7131-7137	9.5	38
240	Tellurium assisted realization of p-type N-doped ZnO. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 242101	3.4	34
239	Suppression of compensation from nitrogen and carbon related defects for p-type N-doped ZnO. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 192106	3.4	33
238	Highly selective and sensitive phosphate anion sensors based on AlGa <sub>N</sub> /Ga <sub>N</sub> high electron mobility transistors functionalized by ion imprinted polymer. <i>Scientific Reports</i> , <b>2016</b> , 6, 27728	4.9	33
237	Broadband hot-carrier dynamics in three-dimensional Dirac semimetal Cd <sub>3</sub> As <sub>2</sub> . <i>Applied Physics Letters</i> , <b>2017</b> , 111, 091101	3.4	32
236	High Quantum Efficiency GaN-Based p-i-n Ultraviolet Photodetectors Prepared on Patterned Sapphire Substrates. <i>IEEE Photonics Technology Letters</i> , <b>2013</b> , 25, 652-654	2.2	32
235	Ultrafast nonlinear photoresponse of single-wall carbon nanotubes: a broadband degenerate investigation. <i>Nanoscale</i> , <b>2016</b> , 8, 9304-9	7.7	32
234	Carbon clusters in N-doped ZnO by metal-organic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 132107	3.4	31
233	Giant Tunability of the Two-Dimensional Electron Gas at the Interface of BaO/SrTiO <sub>3</sub> . <i>Nano Letters</i> , <b>2017</b> , 17, 6878-6885	11.5	29
232	Identification and modulation of electronic band structures of single-phase E <sub>(AlxGa1-x)</sub> 2O <sub>3</sub> alloys grown by laser molecular beam epitaxy. <i>Applied Physics Letters</i> , <b>2018</b> , 113, 041901	3.4	29
231	Tuning the transport behavior of centimeter-scale WTe <sub>2</sub> ultrathin films fabricated by pulsed laser deposition. <i>Applied Physics Letters</i> , <b>2017</b> , 111, 031906	3.4	29
230	Field-dependent carrier trapping induced kink effect in AlGa <sub>N</sub> /Ga <sub>N</sub> high electron mobility transistors. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 173508	3.4	29

229	Demonstration of the p-NiOx/n-Ga2O3 Heterojunction Gate FETs and Diodes With BV2/Ron,sp Figures of Merit of 0.39 GW/cm2 and 1.38 GW/cm2. <i>IEEE Electron Device Letters</i> , <b>2021</b> , 42, 485-488	4.4	28
228	A Reusable and High Sensitivity Nitrogen Dioxide Sensor Based on Monolayer SnSe. <i>IEEE Electron Device Letters</i> , <b>2018</b> , 39, 599-602	4.4	27
227	Great enhancement in the excitonic recombination and light extraction of highly ordered InGaN/GaN elliptic nanorod arrays on a wafer scale. <i>Nanotechnology</i> , <b>2016</b> , 27, 015301	3.4	27
226	Ultrafast free carrier dynamics in black phosphorus-molybdenum disulfide (BP/MoS2) heterostructures. <i>Nanoscale Horizons</i> , <b>2019</b> , 4, 1099-1105	10.8	26
225	Vertically Emitting Indium Phosphide Nanowire Lasers. <i>Nano Letters</i> , <b>2018</b> , 18, 3414-3420	11.5	25
224	Band Alignment and Interface Recombination in NiO/EGa2O3 Type-II p-n Heterojunctions. <i>IEEE Transactions on Electron Devices</i> , <b>2020</b> , 67, 3341-3347	2.9	24
223	Large-Swing a-IGZO Inverter With a Depletion Load Induced by Laser Annealing. <i>IEEE Electron Device Letters</i> , <b>2014</b> , 35, 1034-1036	4.4	24
222	Significant improvements in InGaN/GaN nano-photoelectrodes for hydrogen generation by structure and polarization optimization. <i>Scientific Reports</i> , <b>2016</b> , 6, 20218	4.9	24
221	Significant Performance Improvement in AlGaN Solar-Blind Avalanche Photodiodes by Exploiting the Built-In Polarization Electric Field. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2014</b> , 20, 187-192	3.8	23
220	Exploitation of Polarization in Back-Illuminated AlGaN Avalanche Photodiodes. <i>IEEE Photonics Technology Letters</i> , <b>2013</b> , 25, 1510-1513	2.2	23
219	Influence of thermally diffused aluminum atoms from sapphire substrate on the properties of ZnO epilayers grown by metal-organic chemical vapor deposition. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2011</b> , 29, 03A106	2.9	23
218	Performance of Monolayer Blue Phosphorene Double-Gate MOSFETs from the First Principles. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2019</b> , 11, 20956-20964	9.5	22
217	Transport evidence of 3D topological nodal-line semimetal phase in ZrSiS. <i>Frontiers of Physics</i> , <b>2018</b> , 13, 1	3.7	22
216	Modification of the valence band structures of polar and nonpolar plane wurtzite-GaN by anisotropic strain. <i>Journal of Applied Physics</i> , <b>2009</b> , 106, 023714	2.5	22
215	Ultrahigh Hall mobility and suppressed backward scattering in layered semiconductor Bi2O2Se. <i>Applied Physics Letters</i> , <b>2018</b> , 113, 072106	3.4	21
214	Three-dimensional monolithic micro-LED display driven by atomically thin transistor matrix. <i>Nature Nanotechnology</i> , <b>2021</b> , 16, 1231-1236	28.7	20
213	Tailoring exciton dynamics of monolayer transition metal dichalcogenides by interfacial electron-phonon coupling. <i>Communications Physics</i> , <b>2019</b> , 2,	5.4	19
212	Do all screw dislocations cause leakage in GaN-based devices?. <i>Applied Physics Letters</i> , <b>2020</b> , 116, 062104	3.4	19

211	Direct Demonstration of the Emergent Magnetism Resulting from the Multivalence Mn in a LaMnO <sub>3</sub> Epitaxial Thin Film System. <i>Advanced Electronic Materials</i> , <b>2018</b> , 4, 1800055	6.4	19
210	Manipulable and Hybridized, Ultralow-Threshold Lasing in a Plasmonic Laser Using Elliptical InGa <sub>N</sub> /Ga <sub>N</sub> Nanorods. <i>Advanced Functional Materials</i> , <b>2017</b> , 27, 1703198	15.6	19
209	Temperature-dependent photoluminescence of ZnO films codoped with tellurium and nitrogen. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 103534	2.5	19
208	Efficiency droop behavior of direct current aged GaN-based blue light-emitting diodes. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 163504	3.4	19
207	1.37 kV/12 A NiO/EGa <sub>2</sub> O <sub>3</sub> Heterojunction Diode With Nanosecond Reverse Recovery and Rugged Surge-Current Capability. <i>IEEE Transactions on Power Electronics</i> , <b>2021</b> , 36, 12213-12217	7.2	19
206	Controllable synthesis and magnetotransport properties of Cd <sub>3</sub> As <sub>2</sub> Dirac semimetal nanostructures. <i>RSC Advances</i> , <b>2017</b> , 7, 17689-17696	3.7	18
205	Realization of p-type gallium nitride by magnesium ion implantation for vertical power devices. <i>Scientific Reports</i> , <b>2019</b> , 9, 8796	4.9	18
204	Synthesis of Zinc Aluminate Spinel Film through the Solid-Phase Reaction between Zinc Oxide Film and $\gamma$ -Alumina Substrate. <i>Journal of the American Ceramic Society</i> , <b>2003</b> , 86, 2059-2062	3.8	18
203	Light-Tunable Ferromagnetism in Atomically Thin Fe <sub>3</sub> GeTe <sub>2</sub> Driven by Femtosecond Laser Pulse. <i>Physical Review Letters</i> , <b>2020</b> , 125, 267205	7.4	17
202	Gate Reliability of p-GaN Gate AlGa <sub>N</sub> /Ga <sub>N</sub> High Electron Mobility Transistors. <i>IEEE Electron Device Letters</i> , <b>2019</b> , 40, 379-382	4.4	16
201	High Fill-Factor 4H-SiC Avalanche Photodiodes With Partial Trench Isolation. <i>IEEE Photonics Technology Letters</i> , <b>2016</b> , 28, 2526-2528	2.2	16
200	Enhanced p-type conduction in AlGa <sub>N</sub> grown by metal-source flow-rate modulation epitaxy. <i>Applied Physics Letters</i> , <b>2018</b> , 113, 072107	3.4	16
199	Experimental observation of dual magnetic states in topological insulators. <i>Science Advances</i> , <b>2019</b> , 5, eaav2088	14.3	15
198	Solar-blind ultraviolet AlInN/AlGa <sub>N</sub> distributed Bragg reflectors. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 242112	3.4	15
197	Localized Surface Plasmon-Enhanced Deep-UV Light-Emitting Diodes with Al/Al <sub>2</sub> O <sub>3</sub> Asymmetrical Nanoparticles. <i>Plasmonics</i> , <b>2017</b> , 12, 843-848	2.4	15
196	Suppressed carrier density for the patterned high mobility two-dimensional electron gas at Al <sub>2</sub> O <sub>3</sub> /SrTiO <sub>3</sub> heterointerfaces. <i>Applied Physics Letters</i> , <b>2017</b> , 111, 021602	3.4	14
195	High Quantum Efficiency Back-Illuminated AlGa <sub>N</sub> -Based Solar-Blind Ultraviolet p-i-n Photodetectors. <i>Chinese Physics Letters</i> , <b>2012</b> , 29, 097302	1.8	14
194	Growth of In-rich and Ga-rich InGa <sub>N</sub> alloys by MOCVD and fabrication of InGa <sub>N</sub> -based photoelectrodes. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2010</b> , 7, 1817-1820		14

193	Influence of vapor transport equilibration on the crystal quality and thermal-expansion coefficients of $\text{LiAlO}_2$ . <i>Journal of Applied Physics</i> , <b>2005</b> , 98, 084909	2.5	14
192	Study on strain and piezoelectric polarization of AlN thin films grown on Si. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2005</b> , 23, 628-630	2.9	14
191	Photoluminescence Study of the Photoinduced Phase Separation in Mixed-Halide Hybrid Perovskite $\text{CH}_3\text{NH}_3\text{Pb}(\text{Br})_x(\text{I})_{1-x}$ Crystals Synthesized via a Solvothermal Method. <i>Scientific Reports</i> , <b>2017</b> , 7, 17695	4.9	13
190	Ge composition and temperature dependence of the deposition of SiGe layers. <i>Journal of Applied Physics</i> , <b>1994</b> , 75, 5382-5384	2.5	13
189	High-Voltage Quasi-Vertical GaN Junction Barrier Schottky Diode With Fast Switching Characteristics. <i>IEEE Electron Device Letters</i> , <b>2021</b> , 42, 974-977	4.4	13
188	Highly efficient solar steam generation by hybrid plasmonic structured TiN/mesoporous anodized alumina membrane. <i>Journal of Materials Research</i> , <b>2018</b> , 33, 3857-3869	2.5	13
187	1.95-kV Beveled-Mesa NiO/ $\text{AlGa}_2\text{O}_3$ Heterojunction Diode With 98.5% Conversion Efficiency and Over Million-Times Overvoltage Ruggedness. <i>IEEE Transactions on Power Electronics</i> , <b>2021</b> , 1-1	7.2	13
186	4H-SiC SACM Avalanche Photodiode With Low Breakdown Voltage and High UV Detection Efficiency. <i>IEEE Photonics Journal</i> , <b>2016</b> , 8, 1-7	1.8	12
185	Characteristics of polarization-doped N-face III-nitride light-emitting diodes. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 073507	3.4	12
184	2.41 kV Vertical P-NiO/n-Ga $_2$ O $_3$ Heterojunction Diodes With a Record Baliga Figure-of-Merit of 5.18 GW/cm $^2$ . <i>IEEE Transactions on Power Electronics</i> , <b>2021</b> , 1-1	7.2	12
183	Electrically tunable terahertz metamaterials with embedded large-area transparent thin-film transistor arrays. <i>Scientific Reports</i> , <b>2016</b> , 6, 23486	4.9	12
182	Ultrafast Orbital-Oriented Control of Magnetization in Half-Metallic La Sr MnO Films. <i>Advanced Materials</i> , <b>2019</b> , 31, e1806443	24	11
181	Topological Phase Transition-Induced Triaxial Vector Magnetoresistance in (BiIn)Se Nanodevices. <i>ACS Nano</i> , <b>2018</b> , 12, 1537-1543	16.7	11
180	Intramolecular Crystal Nucleation Favored by Polymer Crystallization: Monte Carlo Simulation Evidence. <i>Journal of Physical Chemistry B</i> , <b>2016</b> , 120, 6754-60	3.4	11
179	High-Performance 4H-SiC p-i-n Ultraviolet Photodiode With p Layer Formed by Al Implantation. <i>IEEE Photonics Technology Letters</i> , <b>2016</b> , 28, 1189-1192	2.2	11
178	High Sensitive pH Sensor Based on AlInN/GaN Heterostructure Transistor. <i>Sensors</i> , <b>2018</b> , 18,	3.8	11
177	Hybrid Light Emitters and UV Solar-Blind Avalanche Photodiodes based on III-Nitride Semiconductors. <i>Advanced Materials</i> , <b>2020</b> , 32, e1904354	24	11
176	Analysis of Dark Count Mechanisms of 4H-SiC Ultraviolet Avalanche Photodiodes Working in Geiger Mode. <i>IEEE Transactions on Electron Devices</i> , <b>2017</b> , 64, 4532-4539	2.9	11

175	Nontrivial surface state transport in Bi <sub>2</sub> Se <sub>3</sub> topological insulator nanoribbons. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 053108	3.4	10
174	Photoresponsivity of an all-semimetal heterostructure based on graphene and WTe. <i>Scientific Reports</i> , <b>2018</b> , 8, 12840	4.9	10
173	Extreme absorption enhancement in ZnTe:O/ZnO intermediate band core-shell nanowires by interplay of dielectric resonance and plasmonic bowtie nanoantennas. <i>Scientific Reports</i> , <b>2017</b> , 7, 7503	4.9	10
172	An Improved Design for Solar-Blind AlGaIn Avalanche Photodiodes. <i>IEEE Photonics Journal</i> , <b>2017</b> , 9, 1-7	1.8	10
171	Mutually beneficial doping of tellurium and nitrogen in ZnO films grown by metal-organic chemical vapor deposition. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2012</b> , 30, 051508	2.9	10
170	First-principles insights on the electronic and optical properties of ZnO@CNT core@shell nanostructure. <i>Scientific Reports</i> , <b>2018</b> , 8, 15464	4.9	10
169	High-temperature and reliability performance of 4H-SiC Schottky-barrier photodiodes for UV detection. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2015</b> , 33, 040602	1.3	9
168	Electrolyte gate controlled metal-insulator transitions of the CaZrO <sub>3</sub> /SrTiO <sub>3</sub> heterointerface. <i>Applied Physics Letters</i> , <b>2019</b> , 115, 061601	3.4	9
167	Spatially localised luminescence emission properties induced by formation of ring-shaped quasi-potential trap around V-pits in InGaIn epi-layers. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2014</b> , 211, 2823-2827	1.6	9
166	Bandgap renormalization in single-wall carbon nanotubes. <i>Scientific Reports</i> , <b>2017</b> , 7, 11221	4.9	9
165	Temperature-dependent exciton-related transition energies mediated by carrier concentrations in unintentionally Al-doped ZnO films. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 221905	3.4	9
164	GaN MSM photodetectors fabricated on bulk GaN with low dark-current and high UV/visible rejection ratio. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2011</b> , 8, 2473-2475		9
163	Epitaxial growth of ZnO films on (100) and (001) LiAlO <sub>2</sub> substrates by pulsed laser deposition. <i>Journal of Materials Science</i> , <b>2006</b> , 41, 5937-5940	4.3	9
162	Solar-blind ultraviolet photodetector based on vertically aligned single-crystalline Ga <sub>2</sub> O <sub>3</sub> nanowire arrays. <i>Nanophotonics</i> , <b>2020</b> , 9, 4497-4503	6.3	9
161	Electron-Beam-Driven III-Nitride Plasmonic Nanolasers in the Deep-UV and Visible Region. <i>Small</i> , <b>2020</b> , 16, e1906205	11	9
160	High-Responsivity Graphene/4H-SiC Ultraviolet Photodetector Based on a Planar Junction Formed by the Dual Modulation of Electric and Light Fields. <i>Advanced Optical Materials</i> , <b>2020</b> , 8, 2000559	8.1	8
159	Single-crystal GaN layer converted from Ga <sub>2</sub> O <sub>3</sub> films and its application for free-standing GaN. <i>CrystEngComm</i> , <b>2019</b> , 21, 1224-1230	3.3	8
158	A Terahertz Controlled-NOT Gate Based on Asymmetric Rotation of Polarization in Chiral Metamaterials. <i>Advanced Optical Materials</i> , <b>2017</b> , 5, 1700108	8.1	8

157	Intrinsic topological insulator Bi(1.5)Sb(0.5)Te(3-x)Se(x) thin crystals. <i>Scientific Reports</i> , <b>2015</b> , 5, 7931	4.9	8
156	A modified simplified coherent potential approximation model of band gap energy of IIIV ternary alloys. <i>Science China: Physics, Mechanics and Astronomy</i> , <b>2012</b> , 55, 400-403	3.6	8
155	Thermal pretreatment of sapphire substrates prior to ZnO buffer layer growth. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2013</b> , 31, 051203	1.3	8
154	Mn incorporation induced changes on structure and properties of N-doped ZnO. <i>Journal of Applied Physics</i> , <b>2009</b> , 106, 113710	2.5	8
153	Self-assembly of Polyaniline: Mechanism Study. <i>Chinese Journal of Chemical Physics</i> , <b>2008</b> , 21, 187-192	0.9	8
152	Simulation model to very low pressure chemical vapor deposition of SiGe alloy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>1996</b> , 14, 3256-3260	2.9	8
151	Evidence for ferromagnetic coupling at the doped topological insulator/ferrimagnetic insulator interface. <i>AIP Advances</i> , <b>2016</b> , 6, 055813	1.5	8
150	3.4-kV AlGaIn/GaN Schottky Barrier Diode on Silicon Substrate With Engineered Anode Structure. <i>IEEE Electron Device Letters</i> , <b>2021</b> , 42, 208-211	4.4	8
149	VT Shift and Recovery Mechanisms of p-GaN Gate HEMTs Under DC/AC Gate Stress Investigated by Fast Sweeping Characterization. <i>IEEE Electron Device Letters</i> , <b>2021</b> , 42, 1508-1511	4.4	8
148	Unsaturated magnetoconductance of epitaxial La <sub>0.7</sub> Sr <sub>0.3</sub> MnO <sub>3</sub> thin films in pulsed magnetic fields up to 60 T. <i>AIP Advances</i> , <b>2017</b> , 7, 056404	1.5	7
147	4H-SiC Ultraviolet Avalanche Photodiodes With Small Gain Slope and Enhanced Fill Factor. <i>IEEE Photonics Journal</i> , <b>2017</b> , 9, 1-8	1.8	7
146	Investigation of the Electroluminescence Mechanism of GaN-Based Blue and Green Light-Emitting Diodes with Junction Temperature Range of 120B73 K. <i>Applied Sciences (Switzerland)</i> , <b>2020</b> , 10, 444	2.6	7
145	Highly Enhanced Inductive Current Sustaining Capability and Avalanche Ruggedness in GaN p-i-n Diodes With Shallow Bevel Termination. <i>IEEE Electron Device Letters</i> , <b>2020</b> , 41, 469-472	4.4	7
144	Probing the Buried Magnetic Interfaces. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2016</b> , 8, 5752-7	9.5	7
143	Observation of bimolecular recombination in high mobility semiconductor Bi <sub>2</sub> O <sub>2</sub> Se using ultrafast spectroscopy. <i>Applied Physics Letters</i> , <b>2018</b> , 113, 061104	3.4	7
142	Tailored Emission Properties of ZnTe/ZnTe:O/ZnO Core-Shell Nanowires Coupled with an Al Plasmonic Bowtie Antenna Array. <i>ACS Nano</i> , <b>2018</b> , 12, 7327-7334	16.7	7
141	Single Photon Counting Spatial Uniformity of 4H-SiC APD Characterized by SNOM-Based Mapping System. <i>IEEE Photonics Technology Letters</i> , <b>2017</b> , 29, 1603-1606	2.2	7
140	4H-SiC Avalanche Photodiode Linear Array Operating in Geiger Mode. <i>IEEE Photonics Journal</i> , <b>2017</b> , 9, 1-7	1.8	7



139	The temperature dependence of optical properties of InGaN alloys. <i>Science China: Physics, Mechanics and Astronomy</i> , <b>2012</b> , 55, 396-399	3.6	7
138	Bias-Selective Dual-Operation-Mode Ultraviolet Schottky-Barrier Photodetectors Fabricated on High-Resistivity Homoepitaxial GaN. <i>IEEE Photonics Technology Letters</i> , <b>2012</b> , 24, 2203-2205	2.2	7
137	The parameters in the band-anticrossing model for $\text{In}_x\text{Ga}_{1-x}\text{N}_y\text{P}_{1-y}$ before and after annealing. <i>Science China: Physics, Mechanics and Astronomy</i> , <b>2011</b> , 54, 2160-2163	3.6	7
136	Microstructures of AlGaIn/AlN/Si (111) Grown by Metalorganic Chemical Vapor Deposition. <i>Physica Status Solidi A</i> , <b>2002</b> , 191, 137-142		7
135	High- $\kappa$ HfO <sub>2</sub> -Based AlGaIn/GaN MIS-HEMTs With Y <sub>2</sub> O <sub>3</sub> Interfacial Layer for High Gate Controllability and Interface Quality. <i>IEEE Journal of the Electron Devices Society</i> , <b>2020</b> , 8, 15-19	2.3	7
134	Unique Current-Direction-Dependent ON/OFF Switching in BiSbTeSe <sub>2</sub> Topological Insulator-Based Spin Valve Transistors. <i>IEEE Electron Device Letters</i> , <b>2016</b> , 1-1	4.4	7
133	Distinct enhancement of sub-bandgap photoresponse through intermediate band in high dose implanted ZnTe:O alloys. <i>Scientific Reports</i> , <b>2017</b> , 7, 44399	4.9	6
132	Spatial Non-Uniform Hot Carrier Luminescence From 4H-SiC p-i-n Avalanche Photodiodes. <i>IEEE Photonics Technology Letters</i> , <b>2019</b> , 31, 447-450	2.2	6
131	Anion Engineering Enhanced Response Speed and Tunable Spectral Responsivity in Gallium-Oxynitrides-Based Ultraviolet Photodetectors. <i>ACS Applied Electronic Materials</i> , <b>2020</b> , 2, 808-816		6
130	1.4-kV Quasi-Vertical GaN Schottky Barrier Diode With Reverse p-n Junction Termination. <i>IEEE Journal of the Electron Devices Society</i> , <b>2020</b> , 1-1	2.3	6
129	Vertical 4H-SiC n-i-p-n APDs With Partial Trench Isolation. <i>IEEE Photonics Technology Letters</i> , <b>2018</b> , 30, 805-808	2.2	6
128	Polarized Emission From InGaIn/GaN Single Nanorod Light-Emitting Diode. <i>IEEE Photonics Technology Letters</i> , <b>2016</b> , 28, 721-724	2.2	6
127	Effect of Very High-Fluence Proton Radiation on 6H-SiC Photoconductive Proton Detectors. <i>IEEE Electron Device Letters</i> , <b>2019</b> , 40, 1929-1932	4.4	6
126	Demonstration of an AlGaIn-based solar-blind high-voltage photoconductive switch. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2015</b> , 33, 040601	1.3	6
125	Solar-blind ultraviolet band-pass filter based on metal-dielectric multilayer structures. <i>Chinese Physics B</i> , <b>2014</b> , 23, 074201	1.2	6
124	Correlation between microstructure and electrical, optical properties of thermal annealed ITO thin films. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2014</b> , 25, 2287-2291	2.1	6
123	Temperature dependence of polarized electroluminescence side emission from (0001)-oriented blue and violet InGaIn/GaN light-emitting diodes. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 203504	3.4	6
122	Charge transfer dynamics of the CdTe quantum dots fluorescence quenching induced by ferrous (II) ions. <i>Applied Physics Letters</i> , <b>2020</b> , 116, 012105	3.4	6

121	Strong interface-induced spin-charge conversion in YIG/Cr heterostructures. <i>Applied Physics Letters</i> , <b>2020</b> , 117, 112402	3.4	6
120	High-Quality Crystal Growth and Characteristics of AlGa <sub>N</sub> -Based Solar-Blind Distributed Bragg Reflectors with a Tri-layer Period Structure. <i>Scientific Reports</i> , <b>2016</b> , 6, 29571	4.9	6
119	Layered Topological Insulators and Semimetals for Magnetoresistance Type Sensors. <i>Advanced Quantum Technologies</i> , <b>2018</b> , 2, 1800039	4.3	6
118	Avalanche Ruggedness of GaN p-i-n Diodes Grown on Sapphire Substrate. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2018</b> , 215, 1800069	1.6	6
117	Demonstration of Avalanche and Surge Current Robustness in GaN Junction Barrier Schottky Diode With 600-V/10-A Switching Capability. <i>IEEE Transactions on Power Electronics</i> , <b>2021</b> , 36, 12163-12167	7.2	6
116	Ga <sub>2</sub> O <sub>3</sub> /GaN Heterostructural Ultraviolet Photodetectors with Exciton-Dominated Ultranarrow Response. <i>ACS Applied Electronic Materials</i> , <b>2022</b> , 4, 188-196	4	6
115	C-plane Blue Micro-LED with 1.53 GHz Bandwidth for High-speed Visible Light Communication. <i>IEEE Electron Device Letters</i> , <b>2022</b> , 1-1	4.4	6
114	Precise Extraction of Dynamic R <sub>ds(on)</sub> Under High Frequency and High Voltage by a Double-Diode-Isolation Method. <i>IEEE Journal of the Electron Devices Society</i> , <b>2019</b> , 1-1	2.3	5
113	Janus Ga <sub>2</sub> SeTe: A Promising Candidate for Highly Efficient Solar Cells. <i>Solar Rrl</i> , <b>2019</b> , 3, 1900321	7.1	5
112	Reverse leakage current in AlGa <sub>N</sub> -based ultraviolet light-emitting diodes. <i>Science Bulletin</i> , <b>2014</b> , 59, 1276-1279	5	5
111	Temperature dependence of the point defect properties of GaN thin films studied by terahertz time-domain spectroscopy. <i>Science China: Physics, Mechanics and Astronomy</i> , <b>2013</b> , 56, 2059-2064	3.6	5
110	Growth evolution and superparamagnetism of ultrathin Fe films grown on GaN(0001) surfaces. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2011</b> , 208, 2348-2351	1.6	5
109	Structural properties of GaN(0001) epitaxial layers revealed by high resolution X-ray diffraction. <i>Science China: Physics, Mechanics and Astronomy</i> , <b>2010</b> , 53, 68-71	3.6	5
108	Dislocation Clustering and Luminescence Nonuniformity in Bulk GaN and Its Homoepitaxial Film. <i>Journal of Electronic Materials</i> , <b>2010</b> , 39, 2243-2247	1.9	5
107	AlGa <sub>N</sub> -based 330 nm resonant-cavity-enhanced p-i-n junction ultraviolet photodetectors using AlN/AlGa <sub>N</sub> distributed Bragg reflectors. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2010</b> , 7, 1821-1824	5	5
106	Element specific spin and orbital moments of nanoscale CoFeB amorphous thin films on GaAs(100). <i>AIP Advances</i> , <b>2016</b> , 6, 095011	1.5	5
105	Giant Topological Hall Effect in van der Waals Heterostructures of CrTe/BiTe. <i>ACS Nano</i> , <b>2021</b> , 15, 15710-15719	16.7	5
104	Fine Control of the Electric Field Distribution in the Heterostructure Multiplication Region of AlGa <sub>N</sub> Avalanche Photodiodes. <i>IEEE Photonics Journal</i> , <b>2017</b> , 9, 1-7	1.8	4

103	Performance Modulation for Back-Illuminated AlGaIn Ultraviolet Avalanche Photodiodes Based on Multiplication Scaling. <i>IEEE Photonics Journal</i> , <b>2019</b> , 11, 1-7	1.8	4
102	Manipulation of Gilbert damping in ultrathin half-metallic Co <sub>2</sub> FeAl <sub>1+x</sub> by composition-deficiency-compensation. <i>Applied Physics Letters</i> , <b>2020</b> , 116, 212406	3.4	4
101	InGaAs Promising Candidate for High-Electron-Mobility Transistors. <i>IEEE Electron Device Letters</i> , <b>2020</b> , 1-1	4.4	4
100	High-Performance 4H-SiC Schottky Photodiode With Semitransparent Grid-Electrode for EUV Detection. <i>IEEE Photonics Technology Letters</i> , <b>2020</b> , 32, 791-794	2.2	4
99	All-carbon hybrids for high-performance electronics, optoelectronics and energy storage. <i>Science China Information Sciences</i> , <b>2019</b> , 62, 1	3.4	4
98	Interfacial transport homogenization for nanowire ensemble photodiodes by using a tunneling insertion. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 103105	3.4	4
97	Simulation of growing GaN in vertical HVPE reactor. <i>Science China: Physics, Mechanics and Astronomy</i> , <b>2010</b> , 53, 72-75	3.6	4
96	The growth temperatures dependence of optical and electrical properties of InN films <b>2008</b> , 51, 237-242		4
95	Investigations of Sidewall Passivation Technology on the Optical Performance for Smaller Size GaN-Based Micro-LEDs. <i>Crystals</i> , <b>2021</b> , 11, 403	2.3	4
94	High Performance Quasi-Vertical GaN Junction Barrier Schottky Diode with Zero Reverse Recovery and Rugged Avalanche Capability <b>2021</b> ,		4
93	High-voltage photoconductive semiconductor switches fabricated on semi-insulating HVPE GaN:Fe template. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2016</b> , 13, 374-377		4
92	Effects of the Trap Level in the Unintentionally Doped GaN Buffer Layer on Optimized p-GaN Gate AlGaIn/GaN HEMTs. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2018</b> , 215, 1700368	1.6	4
91	Achieving Record High External Quantum Efficiency >86.7% in Solar-Blind Photoelectrochemical Photodetection. <i>Advanced Functional Materials</i> , <b>2020</b> , 1604	15.6	4
90	On-chip engineering of high-dimensional path-entangled states in a quadratic coupled-waveguide system. <i>Physical Review A</i> , <b>2019</b> , 99,	2.6	3
89	Polarization-Independent Indium Phosphide Nanowire Photodetectors. <i>Advanced Optical Materials</i> , <b>2020</b> , 8, 2000514	8.1	3
88	Strain-driven lattice distortion and the resultant magnetic properties of La <sub>0.7</sub> Sr <sub>0.3</sub> MnO <sub>3</sub> /BaTiO <sub>3</sub> superlattices. <i>Applied Physics Letters</i> , <b>2019</b> , 115, 201604	3.4	3
87	Effect of the V/III ratio during buffer layer growth on the yellow and blue luminescence in undoped GaN epilayer. <i>Science China: Physics, Mechanics and Astronomy</i> , <b>2013</b> , 56, 1694-1698	3.6	3
86	Improvements in Microstructure and Leakage Current of High-In-Content InGaIn p-i-n Structure by Annealing. <i>IEEE Photonics Technology Letters</i> , <b>2012</b> , 24, 1478-1480	2.2	3

85	Fabrication of blue and green non-polar InGaN/GaN multiple quantum well light-emitting diodes on LiAlO <sub>2</sub> (100) substrates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2010</b> , 207, 1404-1406	1.6	3
84	Effect of current on the inhomogeneous light emission from AlGaInP-based flip-chip red mini-LEDs. <i>IEEE Electron Device Letters</i> , <b>2022</b> , 1-1	4.4	3
83	Element-specific spin and orbital moments and perpendicular magnetic anisotropy in Ta/CoFeB/MgO structures. <i>Journal of Applied Physics</i> , <b>2020</b> , 127, 063903	2.5	3
82	Synthesis and Properties of InGaN/GaN Multiple Quantum Well Nanowires on Si (111) by Molecular Beam Epitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2020</b> , 217, 1900729	1.6	3
81	Quantum Electronics: Evidence of Both Surface and Bulk Dirac Bands and Anisotropic Nonsaturating Magnetoresistance in ZrSiS (Adv. Electron. Mater. 10/2016). <i>Advanced Electronic Materials</i> , <b>2016</b> , 2,	6.4	3
80	Effects of dissipative substrate on the performances of enhancement mode AlInN/GaN HEMTs. <i>International Journal of Numerical Modelling: Electronic Networks, Devices and Fields</i> , <b>2019</b> , 32, e2482	1	3
79	High-performance normally off p-GaN gate high-electron-mobility transistor with In <sub>0.17</sub> Al <sub>0.83</sub> N barrier layer design. <i>Optical and Quantum Electronics</i> , <b>2021</b> , 53, 1	2.4	3
78	Growth and nitridation of EGa <sub>2</sub> O <sub>3</sub> thin films by Sol-Gel spin-coating epitaxy with post-annealing process. <i>Journal of Sol-Gel Science and Technology</i> , <b>2021</b> , 100, 183-191	2.3	3
77	1.2 kV/25 A Normally off P-N Junction/AlGaIn/GaN HEMTs With Nanosecond Switching Characteristics and Robust Overvoltage Capability. <i>IEEE Transactions on Power Electronics</i> , <b>2022</b> , 37, 26-30	7.2	3
76	Observation of Small Polaron and Acoustic Phonon Coupling in Ultrathin La <sub>0.7</sub> Sr <sub>0.3</sub> MnO <sub>3</sub> /SrTiO <sub>3</sub> Structures. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2019</b> , 13, 1800657	2.5	2
75	Direct observation of reach-through behavior in back-illuminated algan avalanche photodiode with separate absorption and multiplication structure. <i>Journal Physics D: Applied Physics</i> , <b>2020</b> , 53, 425101	3	2
74	Mg acceptor activation mechanism and hole transport characteristics in highly Mg-doped AlGaIn alloys. <i>Chinese Physics B</i> , <b>2020</b> , 29, 058103	1.2	2
73	The Effect of the Original Thickness of Ag in the Graphene/Ag Nanodots Transparent Conductive Layer on the Electrical and Optical Properties of GaN-Based UV-LEDs. <i>IEEE Transactions on Electron Devices</i> , <b>2018</b> , 65, 3803-3808	2.9	2
72	A High-Performance SiO <sub>2</sub> /SiN <sub>x</sub> 1-D Photonic Crystal UV Filter Used for Solar-Blind Photodetectors. <i>IEEE Photonics Journal</i> , <b>2019</b> , 11, 1-7	1.8	2
71	Properties of an AlGaIn/AlN distributed-Bragg-reflector structure. <i>Journal of the Korean Physical Society</i> , <b>2014</b> , 65, 1101-1105	0.6	2
70	Simulation of a new style vertical HVPE system. <i>Science China: Physics, Mechanics and Astronomy</i> , <b>2012</b> , 55, 2434-2438	3.6	2
69	Study of buffer and epitaxy technology in two-step growth of aluminium nitride. <i>Science in China Series D: Earth Sciences</i> , <b>2008</b> , 51, 1881-1885		2
68	Observation of a new ordered structure in GeSi/Si strained layer superlattice. <i>Applied Physics Letters</i> , <b>1992</b> , 61, 79-80	3.4	2

67	Enhancing deep-UV emission at 234 nm by introducing a truncated pyramid AlN/GaN nanostructure with fine-tuned multiple facets.. <i>Nanoscale</i> , <b>2022</b> , 14, 653-662	7.7	2
66	Over 1200 V Normally-OFF p-NiO gated AlGaIn/GaN HEMTs on Si with a Small Threshold Voltage Shift. <i>IEEE Electron Device Letters</i> , <b>2021</b> , 1-1	4.4	2
65	Direct observation of ferrimagnetic ordering in inverse Heusler alloy Mn <sub>2</sub> CoAl. <i>Applied Physics Letters</i> , <b>2020</b> , 117, 012401	3.4	2
64	Bi <sub>2</sub> O <sub>2</sub> Se/Au-Based Schottky Phototransistor With Fast Response and Ultrahigh Responsivity. <i>IEEE Electron Device Letters</i> , <b>2020</b> , 41, 1464-1467	4.4	2
63	Enhanced Stability and Sensitivity of AlGaIn/GaN-HEMTs pH Sensor by Reference Device. <i>IEEE Sensors Journal</i> , <b>2021</b> , 21, 9771-9776	4	2
62	Properties of a CdZnO/ZnO multiple quantum-well light-emitting diode. <i>Journal of the Korean Physical Society</i> , <b>2016</b> , 69, 1219-1224	0.6	2
61	Observation and Modeling of Leakage Current in AlGaIn Ultraviolet Light Emitting Diodes. <i>IEEE Photonics Technology Letters</i> , <b>2019</b> , 31, 1697-1700	2.2	2
60	Impurity band assisted carrier relaxation in Cr doped topological insulator Bi <sub>2</sub> Se <sub>3</sub> . <i>Applied Physics Letters</i> , <b>2021</b> , 118, 081103	3.4	2
59	Band Alignment and Enhanced Interfacial Conductivity Manipulated by Polarization in a Surfactant-Mediated Grown $\beta$ -Ga <sub>2</sub> O <sub>3</sub> /In <sub>2</sub> O <sub>3</sub> Heterostructure. <i>ACS Applied Electronic Materials</i> , <b>2021</b> , 3, 795-803	4	2
58	70- $\mu$ m-Body Ga <sub>2</sub> O <sub>3</sub> Schottky Barrier Diode with 1.48 K/W Thermal Resistance, 59 A Surge Current and 98.9% Conversion Efficiency. <i>IEEE Electron Device Letters</i> , <b>2022</b> , 1-1	4.4	2
57	M-Plane $\beta$ -Ga <sub>2</sub> O <sub>3</sub> Solar-Blind Detector With Record-High Responsivity-Bandwidth Product and High-Temperature Operation Capability. <i>IEEE Electron Device Letters</i> , <b>2022</b> , 43, 541-544	4.4	2
56	Demonstration of $\beta$ -Ga <sub>2</sub> O <sub>3</sub> Superjunction-Equivalent MOSFETs. <i>IEEE Transactions on Electron Devices</i> , <b>2022</b> , 69, 2203-2209	2.9	2
55	Unlocking the Single-Domain Heteroepitaxy of Orthorhombic $\beta$ -Ga <sub>2</sub> O <sub>3</sub> via Phase Engineering. <i>ACS Applied Electronic Materials</i> , <b>2022</b> , 4, 461-468	4	2
54	Self-Intercalation Tunable Interlayer Exchange Coupling in a Synthetic van der Waals Antiferromagnet. <i>Advanced Functional Materials</i> , <b>2022</b> , 2202977	15.6	2
53	Current transport mechanisms in Pt/Au Schottky contacts to AlInGaIn using AlGaIn/InGaIn short-period superlattices. <i>Applied Physics A: Materials Science and Processing</i> , <b>2017</b> , 123, 1	2.6	1
52	Optical Performance of Top-Down Fabricated AlGaIn Nanorod Arrays with Multi-Quantum Wells Embedded. <i>Nanoscale Research Letters</i> , <b>2019</b> , 14, 170	5	1
51	After-Pulse Characterizations of Geiger-Mode 4H-SiC Avalanche Photodiodes. <i>IEEE Photonics Technology Letters</i> , <b>2020</b> , 32, 706-709	2.2	1
50	Study of LED Thermal Resistance and TIM Evaluation Using LEDs With Built-in Sensor. <i>IEEE Photonics Technology Letters</i> , <b>2017</b> , 29, 1856-1859	2.2	1

49	Experimental observation on a temperature-induced decoupling between the surface states in topological insulator nanoplates Bi <sub>2</sub> D <sub>15</sub> (TeSe) <sub>3</sub> +0.15. <i>Applied Physics A: Materials Science and Processing</i> , <b>2016</b> , 122, 1	2.6	1
48	The growth and properties of an m-plane InN epilayer on LiAlO <sub>2</sub> (100) by metal-organic chemical vapor deposition. <i>Science China: Physics, Mechanics and Astronomy</i> , <b>2012</b> , 55, 1249-1252	3.6	1
47	Structural and optical characteristics of Al <sub>x</sub> Ga <sub>1-x</sub> N/AlN superlattice. <i>Science in China Series D: Earth Sciences</i> , <b>2009</b> , 52, 332-335		1
46	Carrier transport and luminescence properties of n-type GaN <b>2008</b> , 51, 1046-1052		1
45	Study on growth and properties of novel LiAlO <sub>2</sub> substrate. <i>Science in China Series D: Earth Sciences</i> , <b>2006</b> , 49, 188-193		1
44	Optical and Structural Properties of Si <sub>1-x</sub> C <sub>x</sub> Films. <i>Materials Research Society Symposia Proceedings</i> , <b>1996</b> , 423, 753		1
43	Majority and Minority Carrier Traps in NiO/AlGaIn <sub>0.5</sub> p-n Heterojunction Diode. <i>IEEE Transactions on Electron Devices</i> , <b>2022</b> , 1-7	2.9	1
42	Field-Plated NiO/Ga <sub>2</sub> O <sub>3</sub> p-n Heterojunction Power Diodes With High-Temperature Thermal Stability and Near Unity Ideality Factors. <i>IEEE Journal of the Electron Devices Society</i> , <b>2021</b> , 1-1	2.3	1
41	Optimization of annealing conditions for Ag/p-GaN ohmic contacts. <i>Applied Physics A: Materials Science and Processing</i> , <b>2021</b> , 127, 870	2.6	1
40	Low-Voltage p-i-n GaN-Based Alpha-Particle Detector With High Energy Resolution. <i>IEEE Electron Device Letters</i> , <b>2021</b> , 1-1	4.4	1
39	Electrically tunable terahertz metamaterials with embedded large-area transparent thin-film transistor arrays		1
38	Property manipulation through pulsed laser annealing in high dose Mg-implanted GaN. <i>Journal of Applied Physics</i> , <b>2020</b> , 128, 235704	2.5	1
37	Different I <sub>V</sub> Behaviors and Leakage Current Mechanisms in AlGaIn Solar-Blind Ultraviolet Avalanche Photodiodes. <i>ACS Applied Electronic Materials</i> , <b>2020</b> , 2, 2716-2720	4	1
36	High sensitivity x-ray detectors based on 4H-SiC p-i-n structure with 80 nm thick intrinsic layer. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2021</b> , 39, 022202	1.3	1
35	Vertical Field-Plated NiO/Ga <sub>2</sub> O <sub>3</sub> Heterojunction Power Diodes <b>2021</b> ,		1
34	High-Reflectivity Mg/Al Ohmic Contacts on n-GaN. <i>IEEE Photonics Technology Letters</i> , <b>2021</b> , 33, 347-349	2.2	1
33	A High Quantum Efficiency Narrow-Band UV-B AlGaIn p-i-n Photodiode With Polarization Assistance. <i>IEEE Photonics Journal</i> , <b>2021</b> , 13, 1-8	1.8	1
32	A method of applying compressive pre-stress to AlGaIn barrier in AlGaIn/GaN heterostructures by depositing an additional thermally mismatched dielectric. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2016</b> , 213, 2474-2478	1.6	1

31	Enhanced InGaN/GaN photoelectrodes for visible-light-driven hydrogen generation by surface roughening. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2016</b> , 213, 2704-2708	1.6	1
30	Effective suppression of the high temperature DC performance degradation of AlInN/GaN HEMTs by back barrier. <i>International Journal of Numerical Modelling: Electronic Networks, Devices and Fields</i> , <b>2018</b> , 31, e2299	1	1
29	Investigation on the Activation Energy of Device Degradation and Switching Time in AlGaIn/GaN HEMTs for High-Frequency Application. <i>IEEE Journal of the Electron Devices Society</i> , <b>2019</b> , 1-1	2.3	0
28	Realization of regular resonance mode in GaN-based polygonal microdisks on Si. <i>Journal of Applied Physics</i> , <b>2020</b> , 127, 113102	2.5	0
27	InGaIn/GaN multi-quantum-well-based light-emitting and photodetective dual-functional devices. <i>Frontiers of Optoelectronics in China</i> , <b>2009</b> , 2, 442-445		0
26	GeSi/Si hetero-nanocrystals and the applications in MOSFET memories. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2009</b> , 6, 677-680		0
25	1000-W Resistive Energy Dissipating Capability Against Inductive Transients Demonstrated in Non-Avalanche AlGaIn/GaN Schottky Diode. <i>IEEE Electron Device Letters</i> , <b>2021</b> , 42, 1743-1746	4.4	0
24	Electronic properties of arsenene nanoribbons for FET application. <i>Optical and Quantum Electronics</i> , <b>2020</b> , 52, 1	2.4	0
23	Electrode-Dependent Electrical Properties of Detection-Band Tunable Ultraviolet Photodetectors Based on Ga <sub>2</sub> O <sub>3</sub> /GaN Heterostructures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2021</b> , 218, 2100166	1.6	0
22	Tuning interfacial spin pump in Ta/CoFeB/MgO films by ultrafast laser pulse. <i>Applied Physics Letters</i> , <b>2021</b> , 119, 092404	3.4	0
21	Epitaxial Growth and Characteristics of Nonpolar a-Plane InGaIn Films with Blue-Green-Red Emission and Entire In Content Range. <i>Chinese Physics Letters</i> , <b>2022</b> , 39, 048101	1.8	0
20	4H-SiC n-i-p extreme ultraviolet detector with gradient doping-induced surface junction. <i>IEEE Electron Device Letters</i> , <b>2022</b> , 1-1	4.4	0
19	Effect of Superparamagnetic Fe <sub>3</sub> O <sub>4</sub> Nanoparticles on Schottky Barriers of Graphene. <i>IEEE Transactions on Magnetics</i> , <b>2015</b> , 51, 1-4	2	
18	Synthesis and Properties of InGaIn/GaN Multiple Quantum Well Nanowires on Si (111) by Molecular Beam Epitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2020</b> , 217, 2070028	1.6	
17	Light-Emitting Diodes: High Color Rendering Index Hybrid III-Nitride/Nanocrystals White Light-Emitting Diodes (Adv. Funct. Mater. 1/2016). <i>Advanced Functional Materials</i> , <b>2016</b> , 26, 156-156	15.6	
16	Emergent Ferromagnetism: Direct Demonstration of the Emergent Magnetism Resulting from the Multivalence Mn in a LaMnO <sub>3</sub> Epitaxial Thin Film System (Adv. Electron. Mater. 6/2018). <i>Advanced Electronic Materials</i> , <b>2018</b> , 4, 1870030	6.4	
15	Evidence of anisotropic Landau level splitting in topological semimetal ZrSiS under high magnetic fields. <i>Frontiers of Physics</i> , <b>2019</b> , 14, 1	3.7	
14	23.3: Invited Paper: Hybrid III-Nitride/Nanocrystals White Light-Emitting Diodes. <i>Digest of Technical Papers SID International Symposium</i> , <b>2019</b> , 50, 225-227	0.5	

- 13 Interface Magnetic and Electrical Properties of CoFeB /InAs Heterostructures. *IEEE Transactions on Magnetics*, **2017**, 53, 1-4 2
- 12 Determination of Temperature-Dependent Stress State in Thin AlGa<sub>N</sub> Layer of AlGa<sub>N</sub>/Ga<sub>N</sub> HEMT Heterostructures by Near-Resonant Raman Scattering. *Advances in Condensed Matter Physics*, **2015**, 2015, 1-6 1
- 11 Charge trapping memory devices employing multi-layered Ge/Si nanocrystals for storage fabricated with ALD and PLD methods. *Frontiers of Optoelectronics in China*, **2011**, 4, 146-149
- 10 Compressive and Tensile Strain Effects on Atomic Distribution in Strained Si<sub>0.8</sub>Ge Alloys. *Physica Status Solidi A*, **1997**, 160, 3-10
- 9 Optical properties of InN films grown by MOCVD. *Frontiers of Optoelectronics in China*, **2008**, 1, 341-344
- 8 Microstructure and Physical Properties of GaN Films on Sapphire Substrates. *Materials Research Society Symposia Proceedings*, **1999**, 595, 1
- 7 The Growth and In-Situ Doping of SiGe/Si Strained Heterostructures by RTP/VLP-CVD. *Materials Research Society Symposia Proceedings*, **1994**, 342, 57
- 6 Microstructure and Physical Properties of GaN Films on Sapphire Substrates. *MRS Internet Journal of Nitride Semiconductor Research*, **2000**, 5, 245-251
- 5 Improved Performance of Hybrid Organic/Inorganic p-n Heterojunction White Light-Emitting Diodes with 4,4'-Cyclohexane-1,1-diylbis[N,N-bis(4-methylphenyl)aniline] as a Multifunctional Hole Transport Layer. *Physica Status Solidi (A) Applications and Materials Science*, **2020**, 217, 1900763 1.6
- 4 Improved Performance of Hybrid Organic/Inorganic p-n Heterojunction White Light-Emitting Diodes with 4,4'-Cyclohexane-1,1-diylbis[N,N-bis(4-methylphenyl)aniline] as a Multifunctional Hole Transport Layer. *Physica Status Solidi (A) Applications and Materials Science*, **2020**, 217, 2070029 1.6
- 3 Improved Schottky contacts to InGa<sub>N</sub> alloys by a photoelectrochemical treatment. *Physica Status Solidi (A) Applications and Materials Science*, **2016**, 213, 1034-1038 1.6
- 2 46.4: Fabrication of InGa<sub>N</sub>/Ga<sub>N</sub>-based nano-LEDs for display applications. *Digest of Technical Papers SID International Symposium*, **2021**, 52, 568-568 0.5
- 1 3-D Simulation Study of a Normally-OFF Ga<sub>N</sub> Lateral Multi-Channel JFET With Optimized Electrical Field Transfer Terminal Structure. *IEEE Transactions on Electron Devices*, **2022**, 69, 1918-1923 2.9